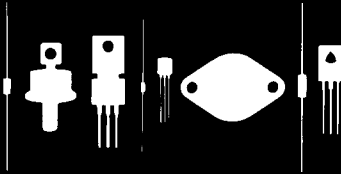


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145 Adams Avenue  
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2N3819

N-CHANNEL SILICON JUNCTION FET

JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3819 type is a Silicon N-Channel Junction Field Effect Transistor designed for RF Amplifier and mixer applications.

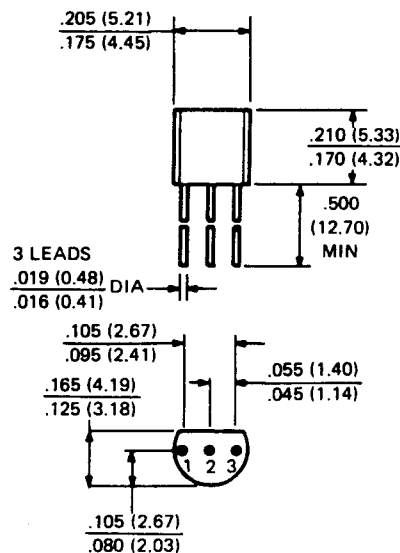
MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNIT
Drain-Gate Voltage	$V_{GD}$	25	V
Drain-Source Voltage	$V_{DS}$	25	V
Gate-Source Voltage (Reverse)	$V_{GS}$	25	V
Gate Current	$I_G$	10	mA
Power Dissipation	$P_D$	360	mW
Operating and Storage Junction Temperature	$T_J, T_{STG}$	-65 TO +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
$I_{DSS}$	$V_{DS}=15\text{V}$	2	20	mA
$I_{GSS}$	$V_{GS}=15\text{V}$		2.0	nA
$I_{GSS}$	$V_{GS}=15\text{V}, T_A=100^\circ\text{C}$		2.0	$\mu\text{A}$
$BV_{GSS}$	$I_G=1.0\mu\text{A}$	25		V
$V_{GS}$	$V_{DS}=15\text{V}, I_D=200\mu\text{A}$	0.5	7.5	V
$V_{GS(OFF)}$	$V_{DS}=15\text{V}, I_D=2.0\text{nA}$		8.0	V
$C_{iss}$	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		8.0	pF
$C_{rss}$	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		4.0	pF
$\tau_{yfs1}$	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$	2000	6500	$\mu\text{ho}$
$\tau_{yfs1}$	$V_{DS}=15\text{V}, V_{GS}=0, f=100\text{MHz}$	1600		$\mu\text{ho}$
$\tau_{yos1}$	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{kHz}$		50	$\mu\text{ho}$

OUTLINE DRAWING:



LEAD CODE:

1. DRAIN
2. GATE
3. SOURCE